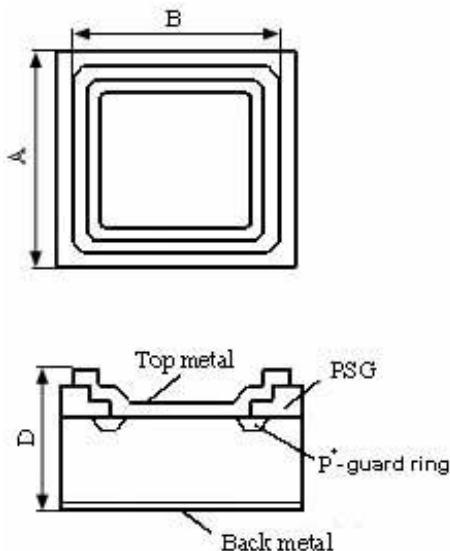




10A/40V. Die Size-90mil.

Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10\text{mA}$	$V_{BR}$	V	40	45
Average Rectified Forward Current	$I_{F(AV)}$	A	10,0	-
DC Forward Voltage @ $25^\circ\text{C}$ , $I_F=10,0\text{A}$	$V_F$	V	0,54	0,52
Maximum Reverse Current @ $25^\circ\text{C}$ , $V_R=45\text{V}$ @ $25^\circ\text{C}$ , $V_R=40\text{V}$ @ $125^\circ\text{C}$ , $V_R=40\text{V}$	$I_R$	mA	- 0,080 45,0	0,080 0,060 40,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}$	A	150	-
Peak Repetitive Reverse Surge Current @ $2,0\mu\text{s}$ , $f=1\text{kHz}$ ., $T_J<150^\circ\text{C}$ .	$I_{RRM}$	A	3,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	$\pm 8$ (contact)	
Voltage Rate of Change	$dV/dt$	$\text{V}/\mu\text{s}$	10.000	
Operating Junction Temperature	$T_J$	$^\circ\text{C}$	150	



DIM	ITEM	$\mu\text{m}$
$A_x$ $A_y$	Wafer Form Die Size	2280
$B_x$ $B_y$	Top Metal Size	2140
D	Thickness	350max.
Scribe line Width		80

*Top metal:*  
 a) **Al** – for Wire Bonding;  
 b) **Al-Ni-Ag** – for Soldering.  
 Backside metal: **Ti-Ni-Ag**.